



TS5A22362 0.65-Ω 2-channel SPDT Analog Switches With Negative Signaling Capability

1 Features

- Specified Break-Before-Make Switching
- Negative Signaling Capability: Maximum Swing from -2.75 V to 2.75 V ($V_{CC} = 2.75\text{ V}$)
- Low ON-State Resistance ($0.65\ \Omega$ Typical)
- Low Charge Injection
- Excellent ON-State Resistance Matching
- 2.3-V to 5.5-V Power Supply (V_{CC})
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2500-V Human-Body Model (A114-B, Class II)
 - 1500-V Charged-Device Model (C101)
 - 200-V Machine Model (A115-A)

2 Applications

- Cell Phones
- PDA's
- Portable Instrumentation
- Audio Routing
- Medical Imaging

3 Description

The TS5A22362 is a bidirectional, 2-channel single-pole double-throw (SPDT) analog switch designed to operate from 2.3 V to 5.5 V. The device features negative signal swing capability that allows signals below ground to pass through the switch without distortion. The break-before-make feature prevents signal distortion during the transferring of a signal from one path to another. Low ON-state resistance, excellent channel-to-channel ON-state resistance matching, and minimal total harmonic distortion (THD) performance are ideal for audio applications. The 3.00 mm × 3.00 mm DRC package is also available as a nonmagnetic package for medical imaging application.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TS5A22362	VSON (10)	3.00 mm × 3.00 mm
	DSBGA (10)	1.86 mm × 1.36 mm
	VSSOP (10)	3.00 mm × 3.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Typical Application Schematic

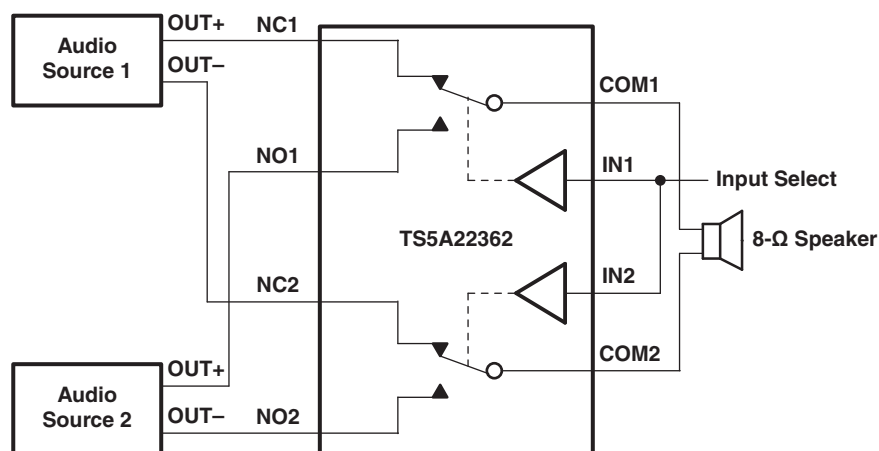


Table of Contents

1 Features	1	8.2 Functional Block Diagram	15
2 Applications	1	8.3 Feature Description	15
3 Description	1	8.4 Device Functional Modes	15
4 Revision History	2	9 Application and Implementation	16
5 Pin Configuration and Functions	3	9.1 Application Information	16
6 Specifications	4	9.2 Typical Application	16
6.1 Absolute Maximum Ratings	4	10 Power Supply Recommendations	18
6.2 ESD Ratings	4	11 Layout	18
6.3 Recommended Operating Conditions	4	11.1 Layout Guidelines	18
6.4 Thermal Information	5	11.2 Layout Example	18
6.5 Electrical Characteristics for 2.5-V Supply	5	12 Device and Documentation Support	19
6.6 Electrical Characteristics for 3.3-V Supply	6	12.1 Community Resources	19
6.7 Electrical Characteristics for 5-V Supply	7	12.2 Trademarks	19
6.8 Typical Characteristics	9	12.3 Electrostatic Discharge Caution	19
7 Parameter Measurement Information	11	12.4 Glossary	19
8 Detailed Description	15	13 Mechanical, Packaging, and Orderable Information	19
8.1 Overview	15		

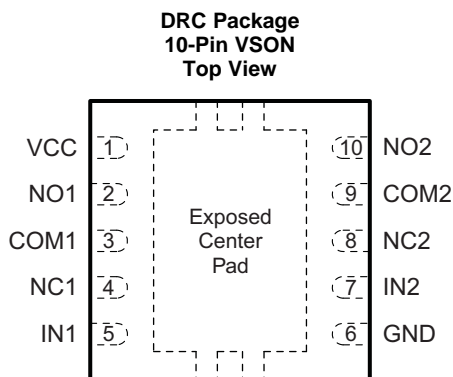
4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

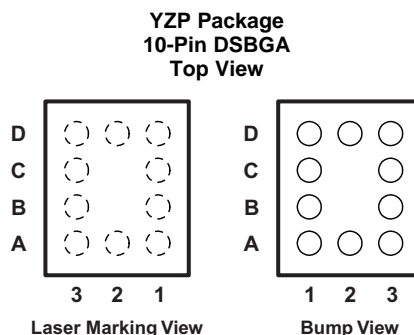
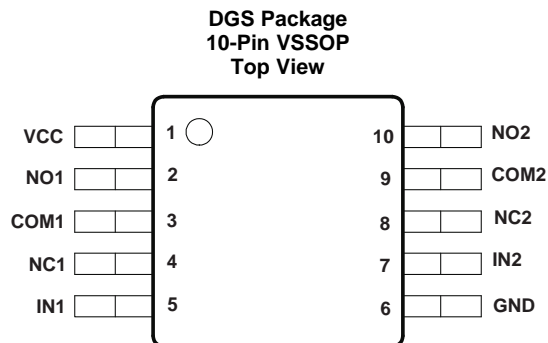
Changes from Revision A (August 2015) to Revision B	Page
• Changed C _L TEST CONDITION value for all THD PARAMETERS from 15 pf to 35 pf.	6

Changes from Original (June 2015) to Revision A	Page
• Changed the Functional Block Diagram.	15

5 Pin Configuration and Functions



*The exposed center pad, if used, must be connected as a secondary GND or left electrically open.



Pin Functions

NAME	PIN			TYPE	DESCRIPTION
	VSON	VSSOP	DSBGA		
VCC	1	1	A2	—	Power Supply
NO1	2	2	A3	I/O	Normally Open (NO) signal path, Switch 1
COM1	3	3	B3	I/O	Common signal path, Switch 1
NC1	4	4	C3	I/O	Normally Closed (NC) signal path, Switch 1
IN1	5	5	D3	I	Digital control pin , Switch 1
GND	6	6	D2	—	Ground
IN2	7	7	D1	I	Digital control pin, Switch 2
NC2	8	8	C1	I/O	Normally Closed (NC) signal path, Switch 2
COM2	9	9	B1	I/O	Common signal path, Switch 2
NO2	10	10	A1	I/O	Normally Open (NO) signal Path, Switch 2

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

			MIN	MAX	UNIT
V _{CC} ⁽²⁾		Supply voltage ⁽³⁾	−0.5	6	V
V _{NC} V _{NO} V _{COM}		Analog voltage ⁽³⁾ ⁽⁴⁾ ⁽⁵⁾	V _{CC} − 6	V _{CC} + 0.5	V
I _{I/OK}	Analog port diode current	V _{NC} , V _{NO} , V _{COM} < 0 or V _{NC} , V _{NO} , V _{COM} > V _{CC}	−50	50	mA
I _{NC} I _{NO} I _{COM}	ON-state switch current	V _{NC} , V _{NO} , V _{COM} = 0 to V _{CC}	−150	150	mA
	ON-state peak switch current ⁽⁶⁾		−300	300	
I _{NC} ⁽³⁾ ⁽⁷⁾ ⁽⁸⁾ I _{NO} ⁽³⁾ ⁽⁷⁾ ⁽⁸⁾ I _{COM} ⁽³⁾ ⁽⁷⁾ ⁽⁸⁾	ON-state switch current	V _{NC} , V _{NO} , V _{COM} = 0 to V _{CC}	−350	350	mA
	ON-state peak switch current ⁽⁶⁾		−500	500	
V _I		Digital input voltage	−0.5	6.5	V
I _{IK}	Digital input clamp current ⁽³⁾ ⁽⁴⁾	V _I < 0	−50	50	mA
I _{CC} I _{GND}		Continuous current through V _{CC} or GND	−100	100	mA
T _{stg}		Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
- (3) All voltages are with respect to ground, unless otherwise specified.
- (4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- (5) This value is limited to 5.5 V maximum.
- (6) Pulse at 1-ms duration < 10% duty cycle.
- (7) $V_{CC} = 3.0$ V to 5.0 V, $T_A = -40^{\circ}\text{C}$ to 85°C .
- (8) For YZP package only.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2500	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	2.3	5.5	V
V_{NC} V_{NO} V_{COM}	Signal path voltage	$V_{CC} - 5.5$	V_{CC}	V
V_{IN}	Digital control	GND	V_{CC}	V

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TS5A22362			UNIT
		DGS (VSSOP)	DRC (VSON)	YZP (DSBGA)	
		10 PINS	10 PINS	10 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	163.3	44.3	90.9	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	56.4	70.1	0.3	°C/W
R _{θJB}	Junction-to-board thermal resistance	83.1	19.3	8.3	°C/W
ψ _{JT}	Junction-to-top characterization parameter	6.8	2.0	3.2	°C/W
ψ _{JB}	Junction-to-board characterization parameter	81.8	19.4	8.3	°C/W

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

6.5 Electrical Characteristics for 2.5-V Supply

V_{CC} = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted) ⁽¹⁾

PARAMETER	TEST CONDITIONS	T _A	V _{CC}	MIN	TYP	MAX	UNIT
Analog Switch							
V _{COM} , V _{NO} , V _{NC}	Analog signal range			V _{CC} – 5.5		V _{CC}	V
R _{on}	ON-state resistance	V _{NC} or V _{NO} = V _{CC} , 1.5 V, V _{CC} – 5.5 V I _{COM} = –100 mA, COM to NO or NC, see Figure 13	25°C Full	2.7 V	0.65 1.3	0.94	Ω
ΔR _{on}	ON-state resistance match between channels	V _{NC} or V _{NO} = 1.5 V, I _{COM} = –100 mA, COM to NO or NC, see Figure 13	25°C Full	2.7 V	0.023 0.15	0.11	Ω
R _{on(flat)}	ON-state resistance flatness	V _{NC} or V _{NO} = V _{CC} , 1.5 V, V _{CC} – 5.5 V I _{COM} = –100 mA, COM to NO or NC, see Figure 13	25°C Full	2.7 V	0.18 0.5	0.46	Ω
I _{NC(OFF)} , I _{NO(OFF)}	NC, NO OFF leakage current	V _{NC} = 2.25 V, V _{CC} – 5.5 V V _{COM} = V _{CC} – 5.5 V, 2.25 V V _{NO} = Open COM to NO or V _{NO} = 2.25 V, V _{CC} – 5.5 V, V _{COM} = V _{CC} – 5.5 V, 2.25 V V _{NC} = Open COM to NC	25°C Full	2.7 V	–50 –375	50 375	nA
I _{COM(ON)}	COM ON leakage current	V _{NC} and V _{NO} = Floating, V _{COM} = V _{CC} , V _{CC} – 5.5 V	25°C Full	2.7 V	–50 –375	50 375	nA
Digital Control Inputs (IN) ⁽²⁾							
V _{IH}	Input logic high		Full		1.4	5.5	V
V _{IL}	Input logic low		Full			0.6	V
I _{IH} , I _{IL}	Input leakage current	V _{IN} = V _{CC} or 0	25°C Full	2.7 V	–250 –250	250 250	nA
Dynamic							
t _{ON}	Turnon time	V _{COM} = V _{CC} , R _L = 300 Ω, C _L = 35 pF, see Figure 17	25°C Full	2.5 V 2.3 V to 2.7 V	44 120	80	ns
t _{OFF}	Turnoff time	V _{COM} = V _{CC} , R _L = 300 Ω, C _L = 35 pF, see Figure 17	25°C Full	2.5 V 2.3 V to 2.7 V	22 70	70	ns
t _{BBM}	Break-before-make time	See Figure 18	25°C	2.5 V	1	7	ns
Q _C	Charge injection	V _{GEN} = 0, R _{GEN} = 0, C _L = 1 nF, see Figure 22	25°C	2.5 V	150		pC
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	V _{NC} or V _{NO} = V _{CC} or GND, See Figure 16	25°C	2.5 V	70		pF
C _{COM(ON)}	NC, NO, COM ON capacitance	V _{COM} = V _{CC} or GND, Switch ON, f = 10 MHz, See Figure 16	25°C	2.5 V	370		pF

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

Electrical Characteristics for 2.5-V Supply (continued)

 $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T_A	V_{CC}	MIN	TYP	MAX	UNIT
C_I	Digital input capacitance	$V_I = V_{CC}$ or GND	See Figure 16	25°C	2.5 V		2.6		pF
BW	Bandwidth	$R_L = 50 \Omega$, -3 dB	See Figure 18	25°C	2.5 V		17		MHz
O_{ISO}	OFF isolation	$R_L = 50 \Omega$	$f = 100 \text{ kHz}$, see Figure 20	25°C	2.5 V		-66		dB
X_{TALK}	Crosstalk	$R_L = 50 \Omega$	$f = 100 \text{ kHz}$, see Figure 21	25°C	2.5 V		-75		dB
THD	Total harmonic distortion	$R_L = 600 \Omega$, $C_L = 35 \text{ pF}$	$f = 20 \text{ Hz to } 20 \text{ kHz}$, see Figure 23	25°C	2.5 V		0.01%		
Supply									
I_{CC}	Positive supply current	V_{COM} and $V_{IN} = V_{CC}$ or GND, V_{NC} and $V_{NO} = \text{Floating}$		25°C	2.7 V		0.2	1.1	μA
				Full				1.3	
I_{CC}	Positive supply current	$V_{COM} = V_{CC} - 5.5 \text{ V}$, $V_{IN} = V_{CC}$ or GND, V_{NC} and $V_{NO} = \text{Floating}$		Full	2.7 V			3.3	μA

6.6 Electrical Characteristics for 3.3-V Supply

 $V_{CC} = 3 \text{ V to } 3.6 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
V _{COM} , V _{NO} , V _{NC}	Analog signal range					V _{CC} − 5.5		V _{CC}	V
R _{on}	ON-state resistance	V _{NC} or V _{NO} ≤ V _{CC} , 1.5 V, V _{CC} − 5.5 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	3 V	0.61		0.87	Ω
				Full				0.97	
ΔR _{on}	ON-state resistance match between channels	V _{NC} or V _{NO} = 1.5 V, I _{COM} = −100 mA,	COM to NO or NC, see Figure 13	25°C	3 V	0.024		0.13	Ω
				Full				0.13	
R _{on(flat)}	ON-state resistance flatness	V _{NC} or V _{NO} ≤ V _{CC} , 1.5 V, V _{CC} − 5.5 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	3 V	0.12		0.46	Ω
				Full				0.5	
I _{NC(OFF)} , I _{NO(OFF)}	NC, NO OFF leakage current	V _{NC} = 3 V, V _{CC} − 5.5 V V _{COM} = V _{CC} − 5.5 V, 3 V V _{NO} = Open COM to NO or V _{NO} = 3 V, V _{CC} − 5.5 V, V _{COM} = V _{CC} − 5.5 V, 3 V V _{NC} = Open COM to NC	See Figure 14	25°C	3.6 V	−50		50	nA
				Full			−375		
I _{COM(ON)}	COM ON leakage current	V _{NC} and V _{NO} = Floating, V _{COM} = V _{CC} , V _{CC} − 5.5 V	COM to NO or NC, see Figure 15	25°C	3.6 V	−50		50	nA
				Full			−375		
DIGITAL CONTROL INPUTS (IN) ⁽²⁾									
V _{IH}	Input logic high			Full		1.4		5.5	V
V _{IL}	Input logic low							0.8	
I _{IH} , I _{IL}	Input leakage current	V _{IN} = V _{CC} or 0		25°C	3.6 V	−250		250	nA
				Full			−250		
DYNAMIC									
t _{ON}	Turnon time	V _{COM} = V _{CC} , R _L = 300 Ω	C _L = 35 pF, see Figure 17	25°C	3.3 V		34	80	ns
				Full	3 V to 3.6 V			120	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number [SCBA004](#).

Electrical Characteristics for 3.3-V Supply (continued)

 $V_{CC} = 3\text{ V to }3.6\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER	TEST CONDITIONS	T_A	V_{CC}	MIN	TYP	MAX	UNIT
t_{OFF} Turnoff time	$V_{COM} = V_{CC}$, $R_L = 300\ \Omega$ $C_L = 35\text{ pF}$, see Figure 17	25°C	3.3 V		19	70	ns
		Full	3 V to 3.6 V			70	
t_{BBM} Break-before-make time	See Figure 18	25°C	3.3 V	1	7		ns
Q_C Charge injection	$V_{GEN} = 0$, $R_{GEN} = 0$ $C_L = 1\text{ nF}$, see Figure 22	25°C	3.3 V		150		pC
$C_{NC(OFF)}$, $C_{NO(OFF)}$ NC, NO OFF capacitance	V_{NC} or $V_{NO} = V_{CC}$ or $V_{CC} - 5.5\text{ V}$ See Figure 16	25°C	3.3 V		70		pF
$C_{COM(ON)}$ NC, NO, COM ON capacitance	$V_{COM} = V_{CC}$ or GND, $f = 10\text{ MHz}$ See Figure 16	25°C	3.3 V		370		pF
C_I Digital input capacitance	$V_I = V_{CC}$ or GND See Figure 16	25°C	3.3 V		2.6		pF
BW Bandwidth	$R_L = 50\ \Omega$, -3 dB Switch ON, see Figure 18	25°C	3.3 V		17.5		MHz
O_{ISO} OFF isolation	$R_L = 50\ \Omega$ $f = 100\text{ kHz}$, see Figure 20	25°C	3.3 V		-68		dB
X_{TALK} Crosstalk	$R_L = 50\ \Omega$ $f = 100\text{ kHz}$, see Figure 21	25°C	3.3 V		-76		dB
THD Total harmonic distortion	$R_L = 600\ \Omega$, $C_L = 35\text{ pF}$ $f = 20\text{ Hz to }20\text{ kHz}$, see Figure 23	25°C	3.3 V		0.008%		
SUPPLY							
I_{CC} Positive supply current	V_{COM} and $V_{IN} = V_{CC}$ or GND, V_{NC} and $V_{NO} = \text{Floating}$	25°C	3.6 V		0.1	1.2	μA
		Full				1.3	
	$V_{COM} = V_{CC} - 5.5\text{ V}$, $V_{IN} = V_{CC}$ or GND, V_{NC} and $V_{NO} = \text{Floating}$	Full	3.6 V			3.4	μA

6.7 Electrical Characteristics for 5-V Supply

 $V_{CC} = 4.5\text{ V to }5.5\text{ V}$, $T_A = -40^\circ\text{C to }85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
V _{COM} , V _{NO} , V _{NC}	Analog signal range					V _{CC} − 5.5		V _{CC}	V
R _{on}	ON-state resistance	V _{NC} or V _{NO} = V _{CC} , 1.6 V, V _{CC} = −5.5 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V	0.52		0.74	Ω
				Full		0.83			
ΔR _{on}	ON-state resistance match between channels	V _{NC} or V _{NO} = 1.6 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V	0.04		0.23	Ω
				Full		0.30			
R _{on(flat)}	ON-state resistance flatness	V _{NC} or V _{NO} = V _{CC} , 1.6 V, V _{CC} = −5.5 V, I _{COM} = −100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V	0.076		0.46	Ω
				Full		0.5			
I _{NC(OFF)} , I _{NO(OFF)}	NC, NO OFF leakage current	V _{NC} = 4.5 V, V _{CC} − 5.5 V, V _{COM} = V _{CC} − 5.5 V, 4.5 V, V _{NO} = Open, COM to NO or V _{NO} = 4.5 V, V _{CC} − 5.5 V, V _{COM} = V _{CC} − 5.5 V, 4.5 V, V _{NC} = Open, COM to NC	See Figure 14	25°C	5.5 V	−50		50	nA
				Full		−375		375	
I _{COM(ON)}	COM ON leakage current	V _{NC} and V _{NO} = Floating, V _{COM} = V _{CC} , V _{CC} − 5.5 V	See Figure 15	25°C	5.5 V	−50		50	nA
				Full		−375		375	
DIGITAL CONTROL INPUTS (IN) ⁽²⁾									

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

Electrical Characteristics for 5-V Supply (continued)

 $V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$, $T_A = -40^\circ\text{C to } 85^\circ\text{C}$ (unless otherwise noted) ⁽¹⁾

PARAMETER		TEST CONDITIONS		T _A	V _{CC}	MIN	TYP	MAX	UNIT	
V _{IH}	Input logic high			Full		2.4		5.5	V	
V _{IL}	Input logic low							0.8		
I _{IH} , I _{IL}	Input leakage current	V _{IN} = V _{CC} or 0		25°C	5.5 V	−250		250	nA	
				Full		−250		250		
DYNAMIC										
t _{ON}	Turnon time	V _{COM} = V _{CC} , R _L = 300 Ω		C _L = 35 pF, see Figure 17		25°C	5 V	27	80	ns
						Full	4.5 V to 5.5 V		80	
t _{OFF}	Turnoff time	V _{COM} = V _{CC} , R _L = 300 Ω		C _L = 35 pF, see Figure 17		25°C	5 V	13	70	ns
						Full	4.5 V to 5.5 V		70	
t _{BBM}	Break-before-make time	V _{NC} = V _{NO} = V _{CC} /2 R _L = 300 Ω		C _L = 35 pF, see Figure 18		25°C	5 V	1	3.5	ns
Q _C	Charge injection	V _{GEN} = 0, R _{GEN} = 0		C _L = 1 nF, see Figure 22		25°C	5 V	10		pC
C _{NC(OFF)} , C _{NO(OFF)}	NC, NO OFF capacitance	V _{NC} or V _{NO} = V _{CC} or V _{CC} − 5.5 V		See Figure 16		25°C	5 V	70		pF
C _{COM(ON)}	NC, NO, COM ON capacitance	V _{COM} = V _{CC} or GND,		See Figure 16		25°C	5 V	370		pF
C _I	Digital input capacitance	V _I = V _{CC} or GND		See Figure 16		25°C	5 V	2.6		pF
BW	Bandwidth	R _L = 50 Ω		See Figure 18		25°C	5 V	18.3		MHz
O _{ISO}	OFF isolation	R _L = 50 Ω		f = 100 kHz, see Figure 20		25°C	5 V	−70		dB
X _{TALK}	Crosstalk	R _L = 50 Ω		f = 100 kHz, see Figure 21		25°C	5 V	−78		dB
THD	Total harmonic distortion	R _L = 600 Ω, C _L = 35 pF		f = 20 Hz to 20 kHz, see Figure 23		25°C	5 V	0.009%		
SUPPLY										
I _{CC}	Positive supply current	V _{COM} and V _{IN} = V _{CC} or GND, V _{NC} and V _{NO} = Floating		25°C	5.5 V		0.2	1.3	μA	
				Full				3.5		
		V _{COM} = V _{CC} − 5.5 V, V _{IN} = V _{CC} or GND, V _{NC} and V _{NO} = Floating		Full				5		

6.8 Typical Characteristics

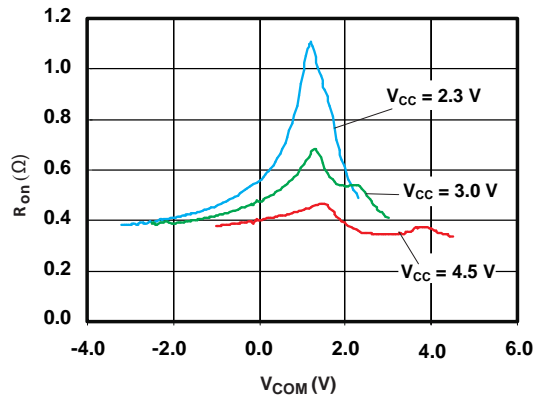


Figure 1. R_{on} vs V_{COM}

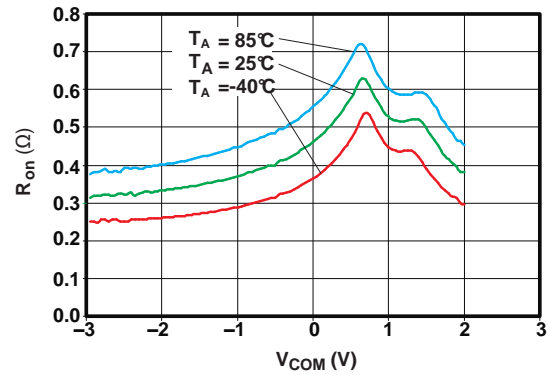


Figure 2. R_{on} vs V_{COM} ($V_{CC} = 2.7$ V)

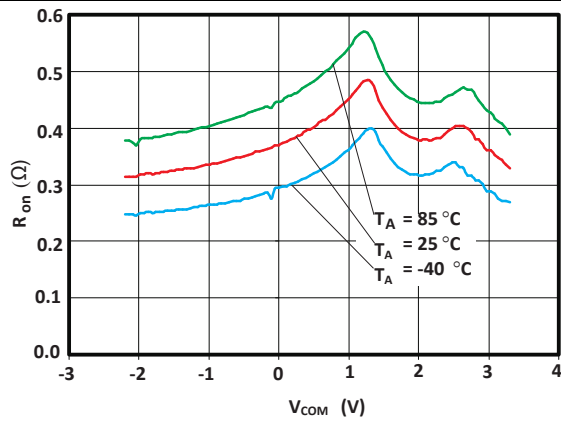


Figure 3. R_{on} vs V_{COM} ($V_{CC} = 3.3$ V)

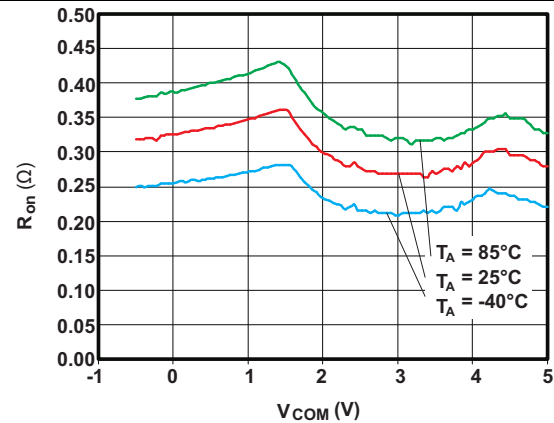


Figure 4. R_{on} vs V_{COM} ($V_{CC} = 5$ V)

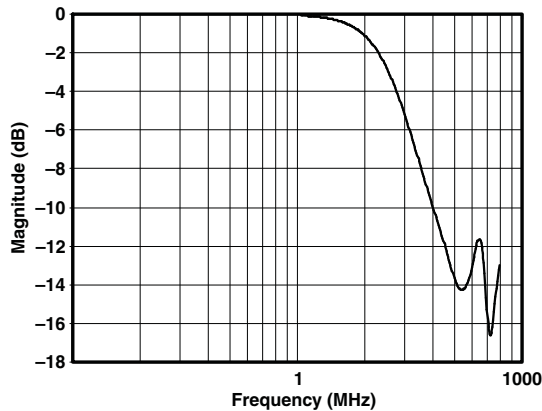


Figure 5. Insertion Loss

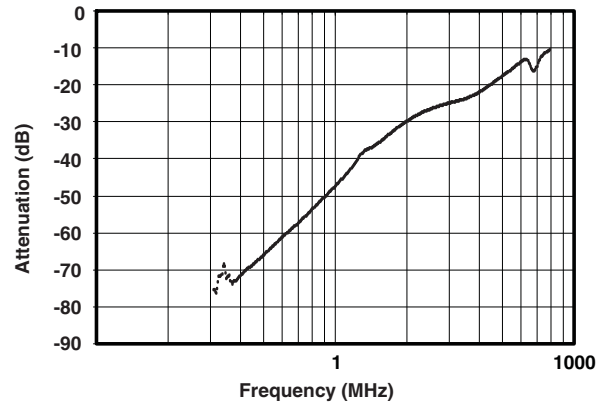


Figure 6. Off Isolation vs Frequency

Typical Characteristics (continued)

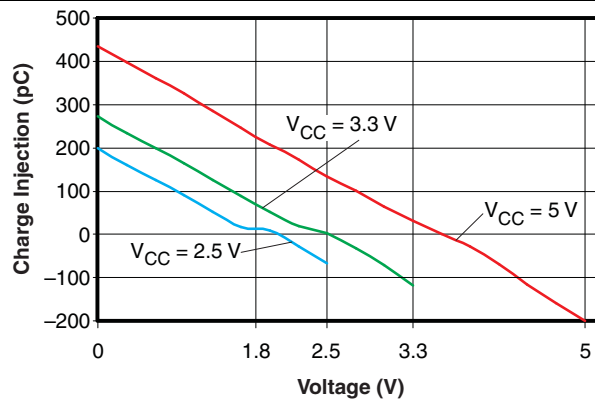


Figure 7. Charge Injection (Q_C) vs V_{COM}

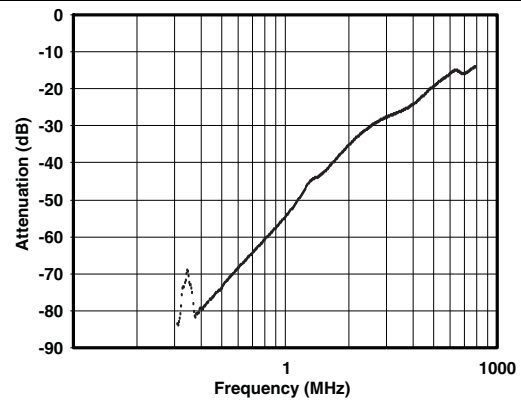


Figure 8. Crosstalk ($V_{CC} = 3.3\text{ V}$)

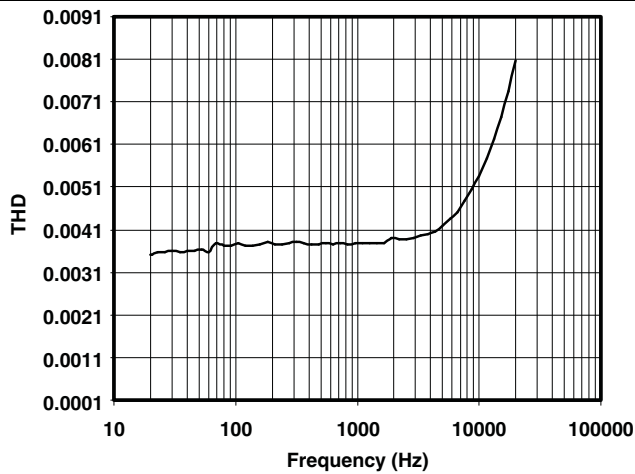


Figure 9. Total Harmonic Distortion vs Frequency

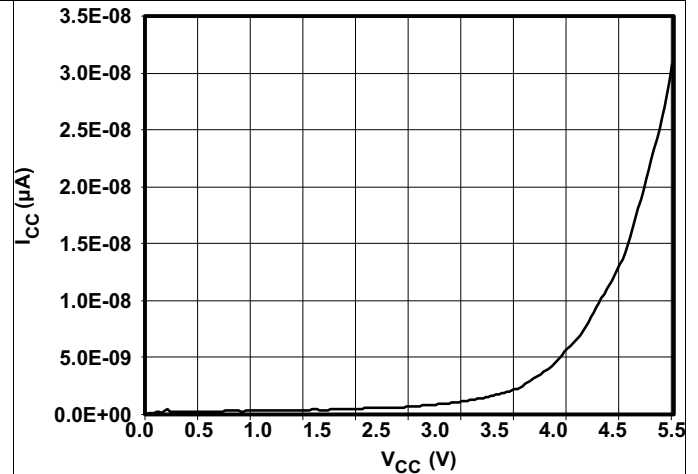


Figure 10. Power-Supply Current vs V_{CC}

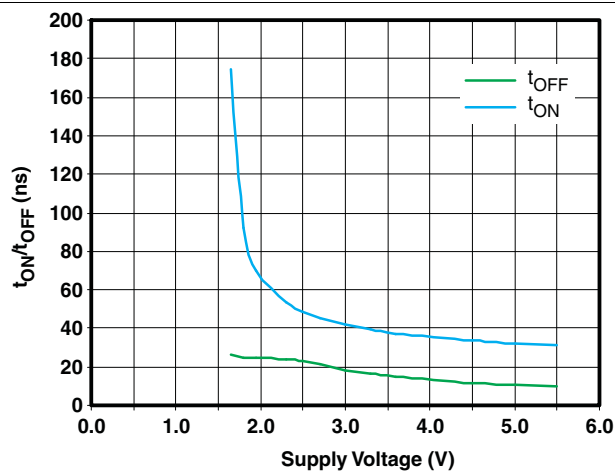


Figure 11. t_{ON} And t_{OFF} vs Supply Voltage

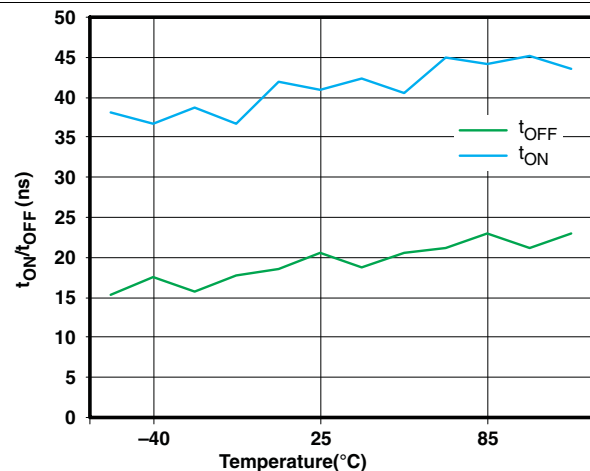


Figure 12. t_{ON} And t_{OFF} vs Temperature (2.5-V Supply)

7 Parameter Measurement Information

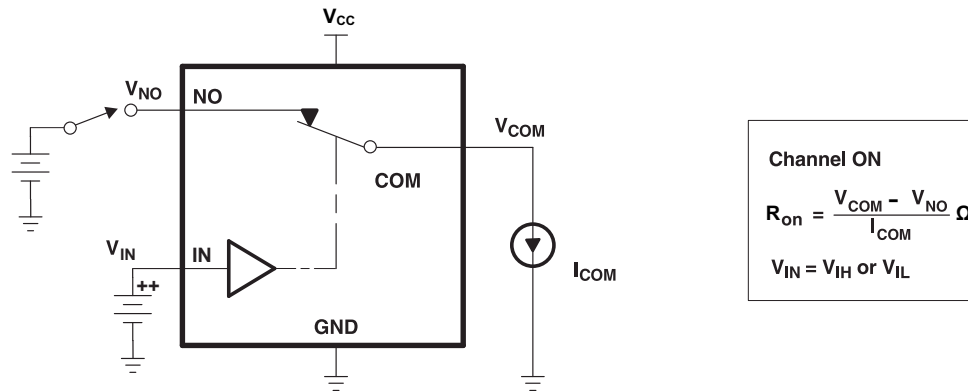


Figure 13. ON-state resistance (R_{on})

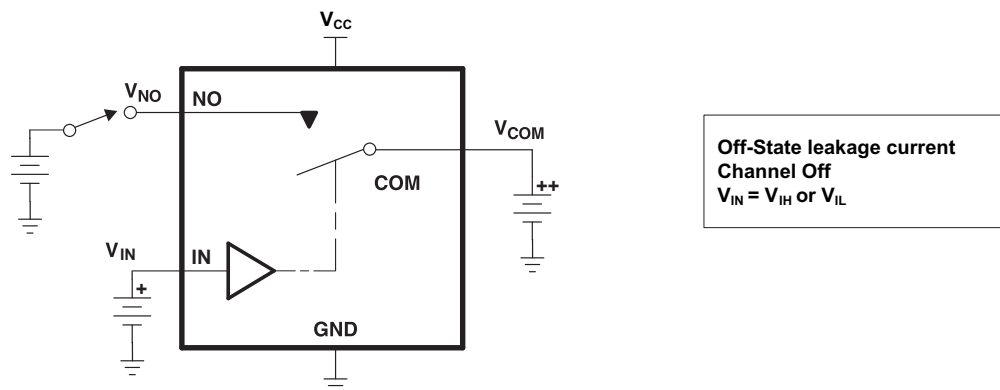
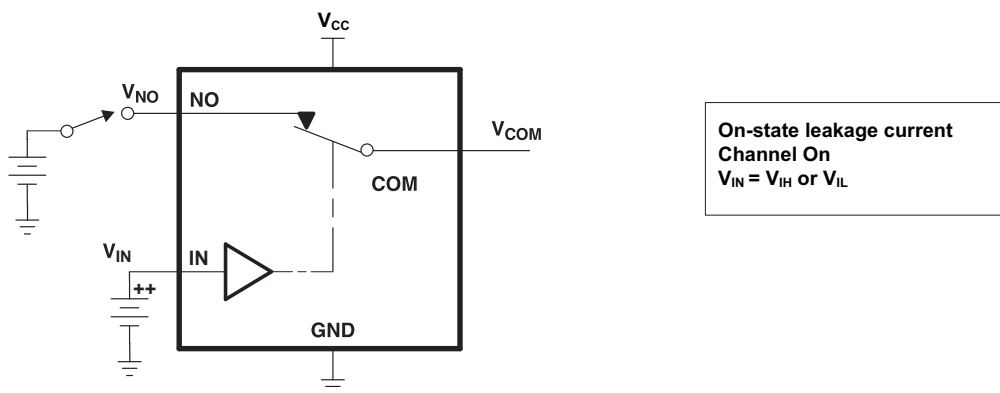


Figure 14. OFF-state leakage current ($I_{COM(OFF)}$, $I_{NO(OFF)}$)



**Figure 15. ON-state leakage current
($I_{COM(ON)}$, $I_{NO(ON)}$)**

Parameter Measurement Information (continued)

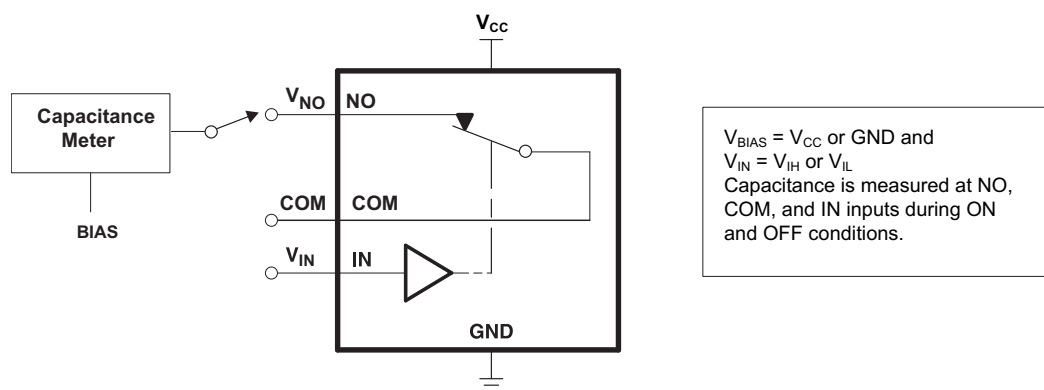
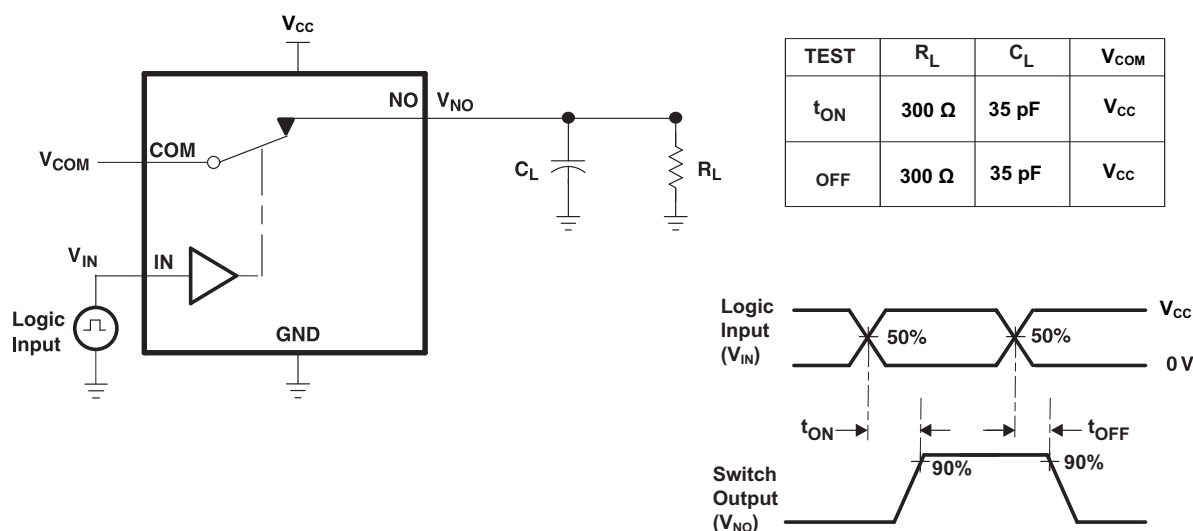


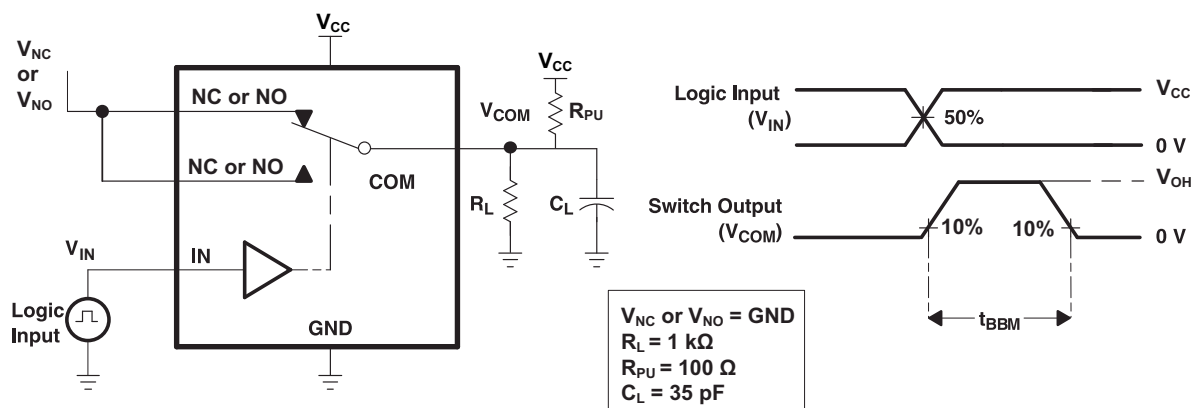
Figure 16. Capacitance
(C_I , $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NO(OFF)}$, $C_{NO(ON)}$)



- A. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.
- B. C_L includes probe and jig capacitance.

Figure 17. Turnon (t_{ON}) and Turnoff time (t_{OFF})

Parameter Measurement Information (continued)



- A. C_L includes probe and jig capacitance.
- B. All input pulses are supplied by generators having the following characteristics: $\text{PRR} \leq 10 \text{ MHz}$, $Z_O = 50 \Omega$, $t_r < 5 \text{ ns}$, $t_f < 5 \text{ ns}$.

Figure 18. Break-Before-Make Time (t_{BBM})

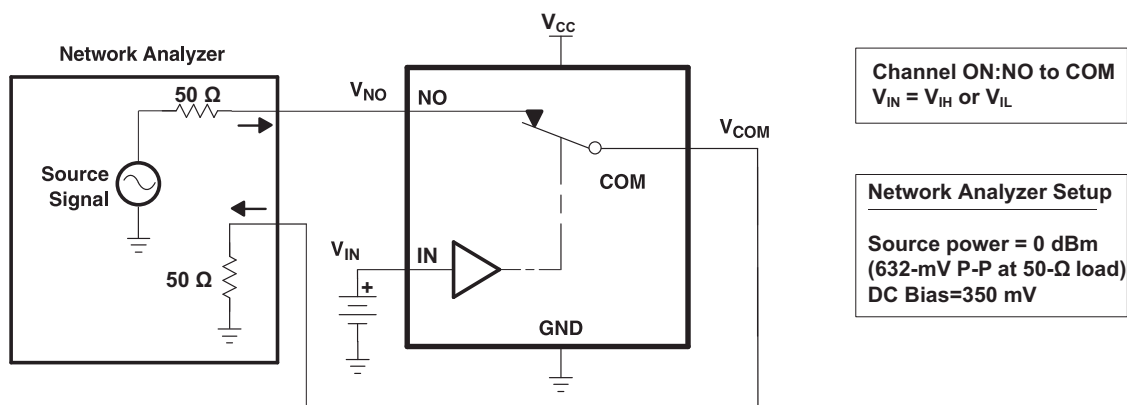


Figure 19. Bandwidth (BW)

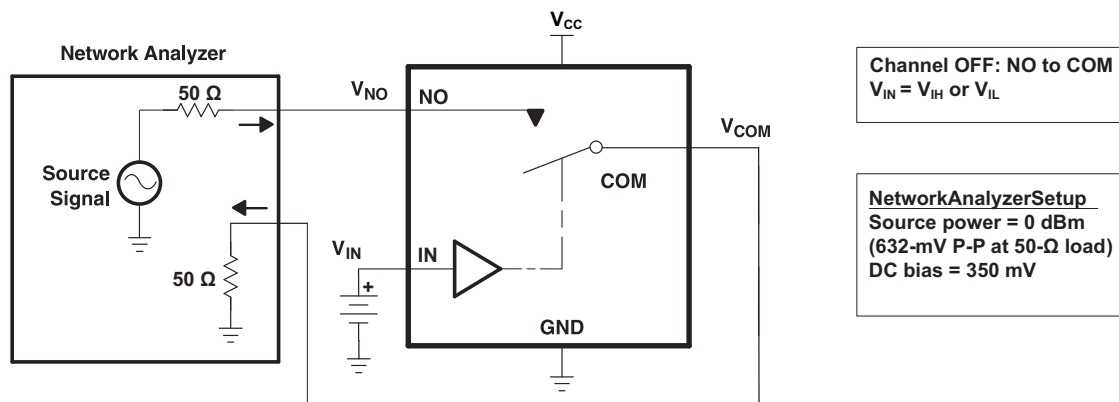


Figure 20. OFF isolation (O_{ISO})

Parameter Measurement Information (continued)

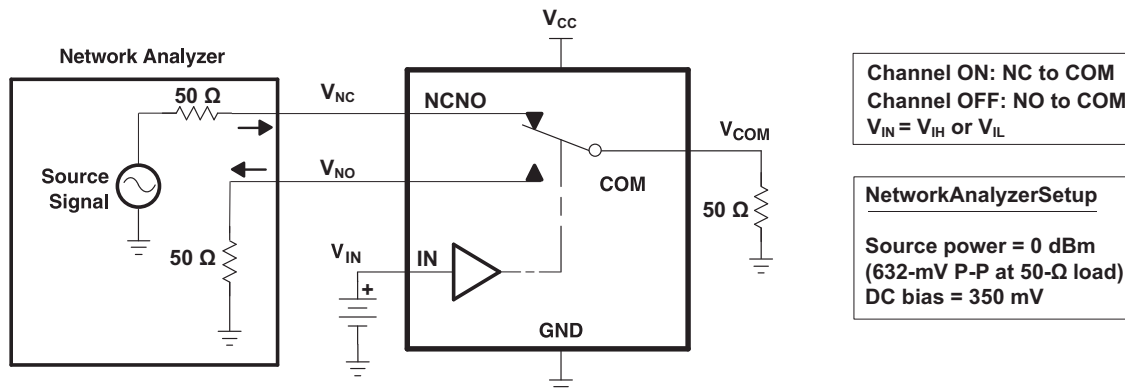
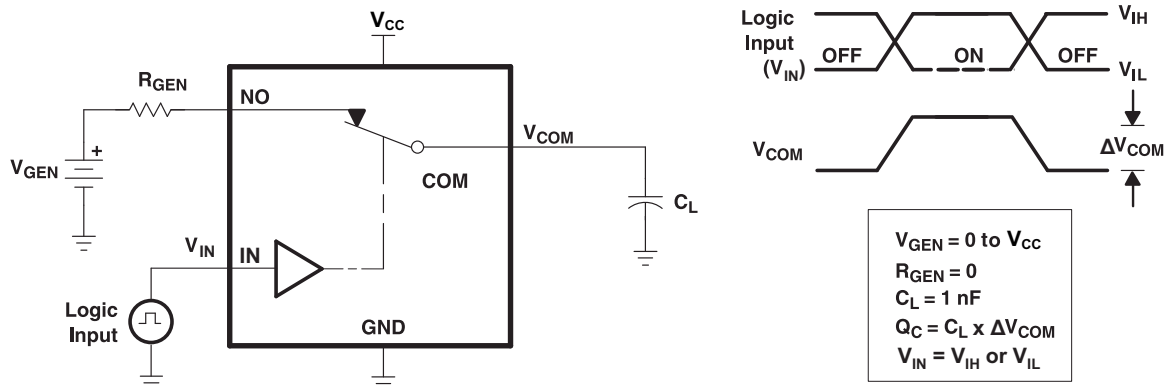


Figure 21. Crosstalk (X_{TALK})



- A. All input pulses are supplied by generators having the following characteristics: $PRR \leq 10$ MHz, $Z_O = 50 \Omega$, $t_r < 5$ ns, $t_f < 5$ ns.
- B. C_L includes probe and jig capacitance.

Figure 22. Charge injection (Q_C)

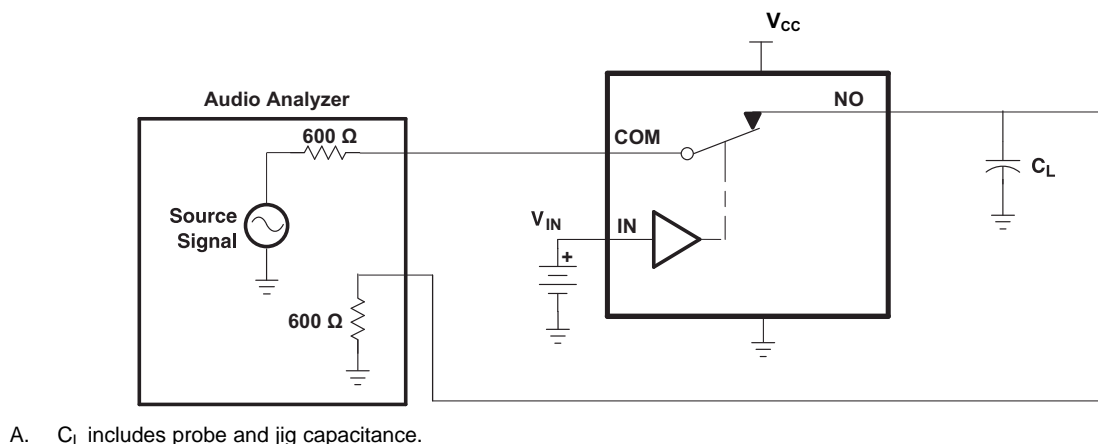
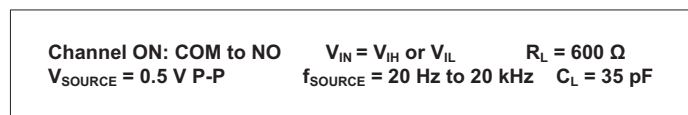


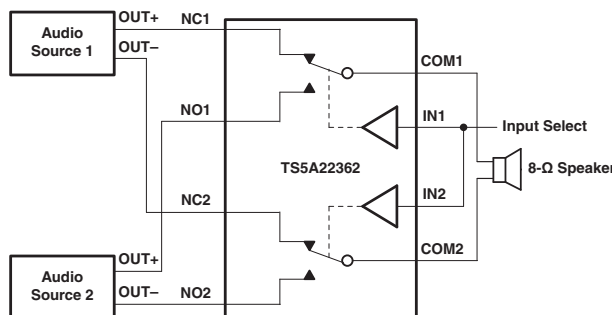
Figure 23. Total Harmonic Distortion (THD)

8 Detailed Description

8.1 Overview

The TS5A22362 is a bidirectional, 2-channel single-pole double-throw (SPDT) analog switches designed to operate from 2.3 V to 5.5 V. The devices feature negative signal capability that allows signals below ground to pass through the switch without distortion. The break-before-make feature prevents signal distortion during the transferring of a signal from one path to another. Low ON-state resistance, excellent channel-to-channel ON-state resistance matching, and minimal total harmonic distortion (THD) performance are ideal for audio applications.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Negative Signaling Capacity

The TS5A22362 dual SPDT switches feature negative signal capability that allows signals below ground to pass through without distortion. These analog switches operate from a single +2.3-V to +5.5-V supply. The input and output signal swing of the device is dependant of the supply voltage V_{CC} : the devices pass signals as high as V_{CC} and as low as $V_{CC} - 5.5$ V, including signals below ground with minimal distortion.

Table 1 shows the input/output signal swing the user can get with different supply voltages.

Table 1. Input/Output signal swing

SUPPLY VOLTAGE, V_{CC}	MINIMUM (V_{NC} , V_{NO} , V_{COM}) = $V_{CC} - 5.5$	MAXIMUM (V_{NC} , V_{NO} , V_{COM}) = V_{CC}
5.5 V	0 V	5.5 V
4.5 V	–1.9 V	4.5 V
3.6 V	–2.5 V	3.6 V
3.0 V	–2.5 V	3.0 V
2.7 V	–2.8 V	2.7 V
2.3 V	–3.2 V	2.3 V

8.4 Device Functional Modes

The function table for TS5A22362 is shown in Table 2

Table 2. Function Table

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Ensure that the device is powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO.

Tie the digitally controlled inputs select pins IN1 and IN2 to VCC or GND to avoid unwanted switch states that could result if the logic control pins are left floating.

All unused digital inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, [SCBA004](#).

9.2 Typical Application

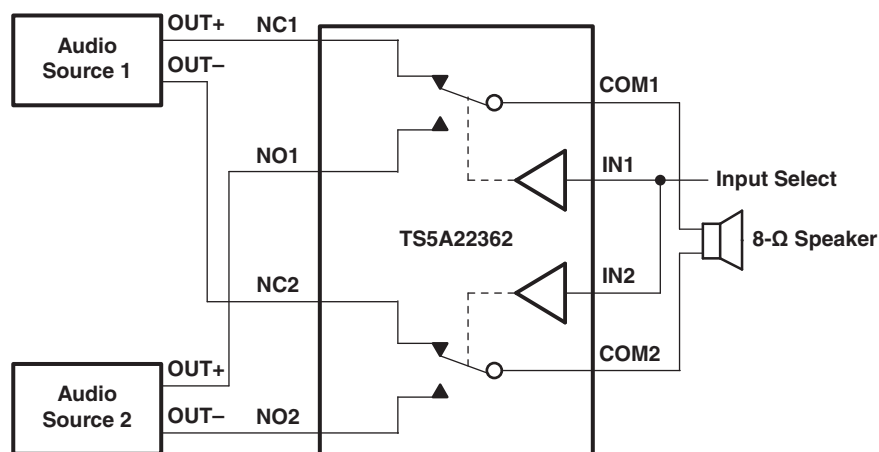


Figure 24. Typical Application

9.2.1 Design Requirements

Tie the digitally controlled inputs select pins IN1 and IN2 to VCC or GND to avoid unwanted switch states that could result if the logic control pins are left floating.

9.2.2 Detailed Design Procedure

Select the appropriate supply voltage to cover the entire voltage swing of the signal passing through the switch because the TS5A22362 operates from a single +2.3-V to +5.5-V supply and the input/output signal swing of the device is dependant of the supply voltage VCC. The device will pass signals as high as VCC and as low as VCC – 5.5 V. Use table 2 as a guide for selecting supply voltage based on the signal passing through the switch.

Ensure that the device is powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO.

Typical Application (continued)

9.2.3 Application Curve

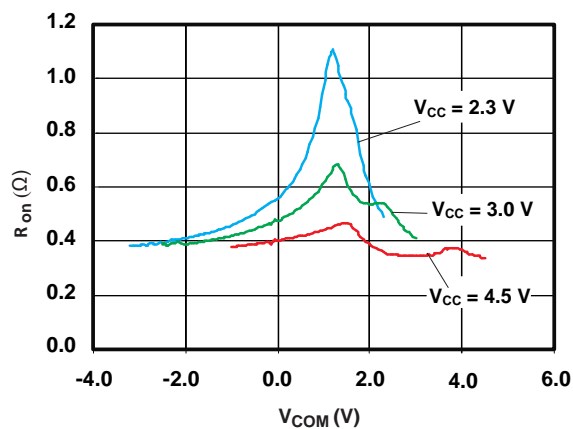


Figure 25. R_{on} vs V_{COM}

10 Power Supply Recommendations

The TS5A22362 operates from a single 2.3-V to 5.5-V supply. The device must be powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO. It is recommended to include a 100- μ s delay after VCC is at voltage before applying a signal on NC and NO paths

It is also good practice to place a 0.1- μ F bypass capacitor on the supply pin VCC to GND to smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

11 Layout

11.1 Layout Guidelines

TI recommends placing a bypass capacitor as close to the supply pin VCC as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

Minimize trace lengths and vias on the signal paths in order to preserve signal integrity.

11.2 Layout Example

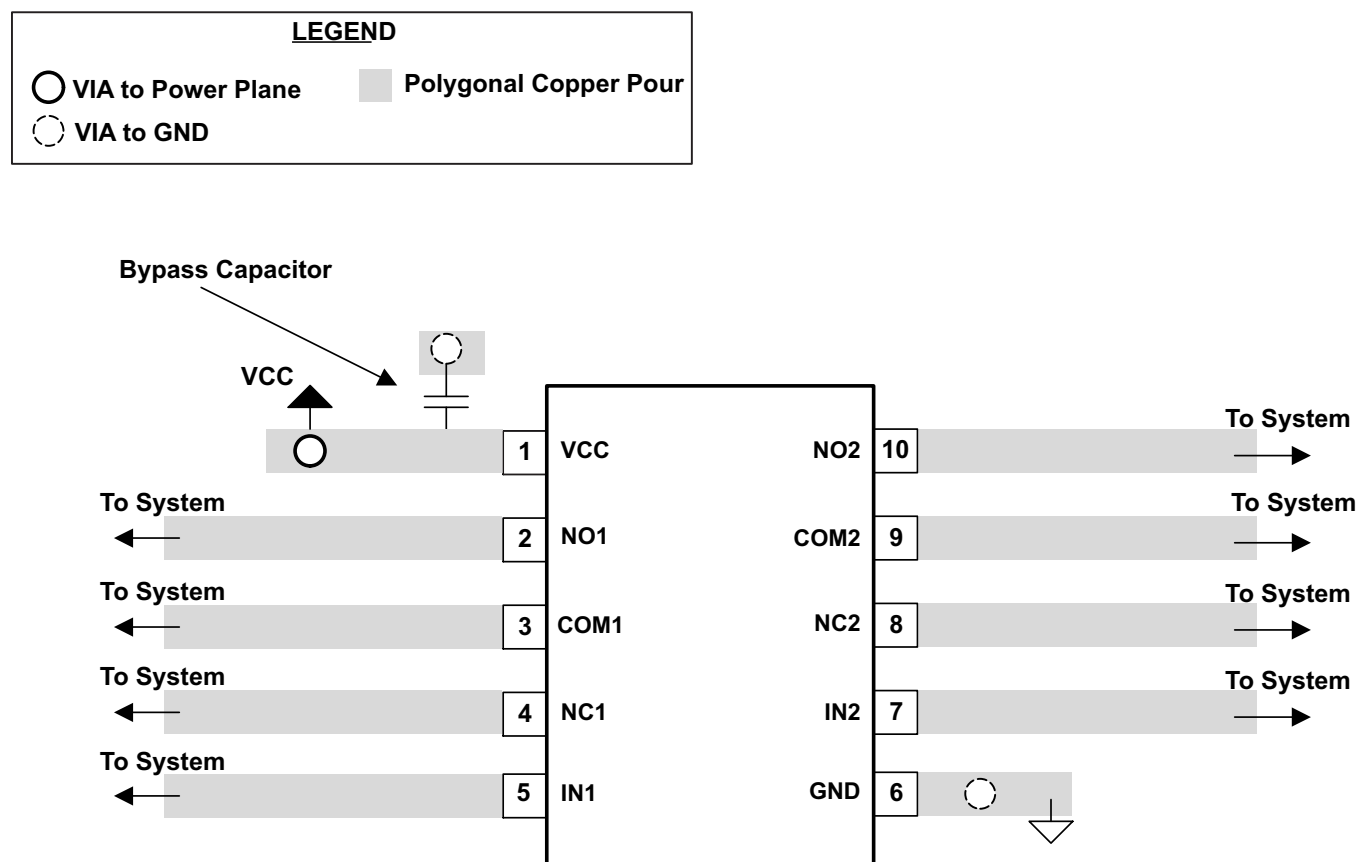


Figure 26. Layout example of TS5A22362

12 Device and Documentation Support

12.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.2 Trademarks

E2E is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.4 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A22362DGSR	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	39R	Samples
TS5A22362DGSRG4	ACTIVE	VSSOP	DGS	10	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	39R	Samples
TS5A22362DRCR	ACTIVE	VSON	DRC	10	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVG	Samples
TS5A22362DRCT-NM	ACTIVE	VSON	DRC	10	250	Green (RoHS & no Sb/Br)	CU SN	Level-2-260C-1 YEAR	-40 to 85	ZVGNM	Samples
TS5A22362YZPR	ACTIVE	DSBGA	YZP	10	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(39 ~ 392)	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A22362DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS5A22362DRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS5A22362DRCT-NM	VSON	DRC	10	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS5A22362YZPR	DSBGA	YZP	10	3000	178.0	9.2	1.49	1.99	0.63	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS

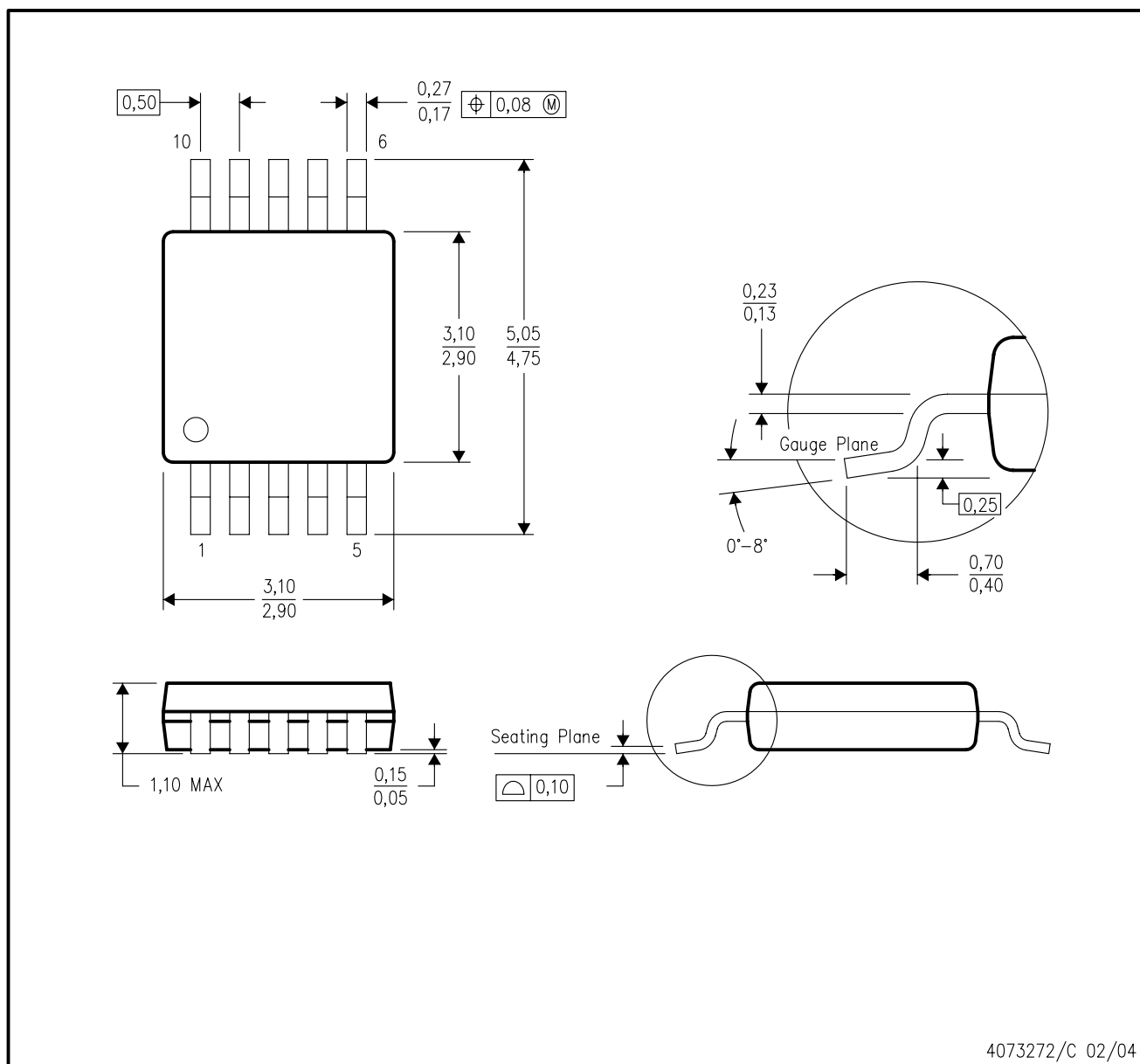


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A22362DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
TS5A22362DRCR	VSON	DRC	10	3000	367.0	367.0	35.0
TS5A22362DRCT-NM	VSON	DRC	10	250	210.0	185.0	35.0
TS5A22362YZPR	DSBGA	YZP	10	3000	220.0	220.0	35.0

DGS (S-PDSO-G10)

PLASTIC SMALL-OUTLINE PACKAGE

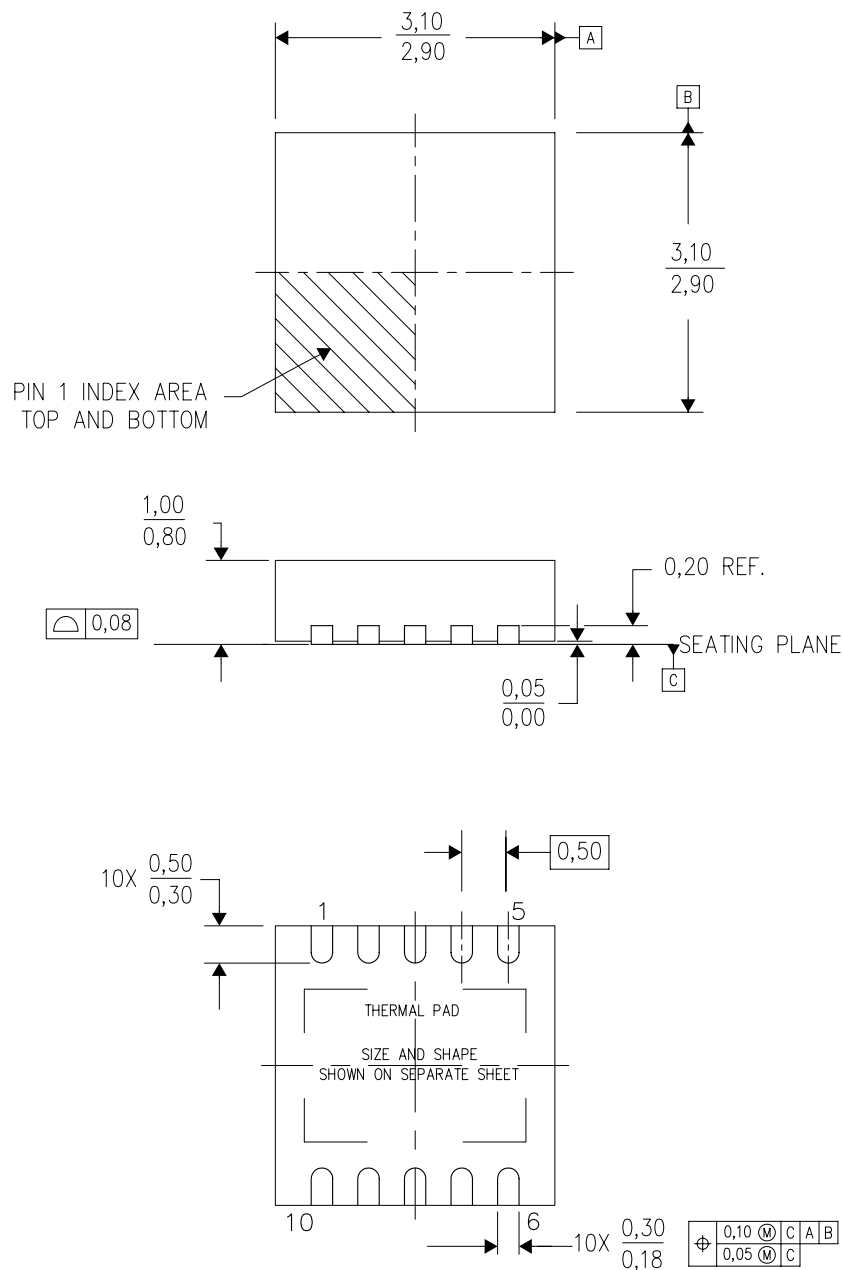


4073272/C 02/04

- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Body dimensions do not include mold flash or protrusion.
 - Falls within JEDEC MO-187 variation BA.

DRC (S-PVSON-N10)

PLASTIC SMALL OUTLINE NO-LEAD



4204102-3/L 09/11

- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - Small Outline No-Lead (SON) package configuration.
 - The package thermal pad must be soldered to the board for thermal and mechanical performance, if present.
 - See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions, if present.

DRC (S-PVSON-N10)

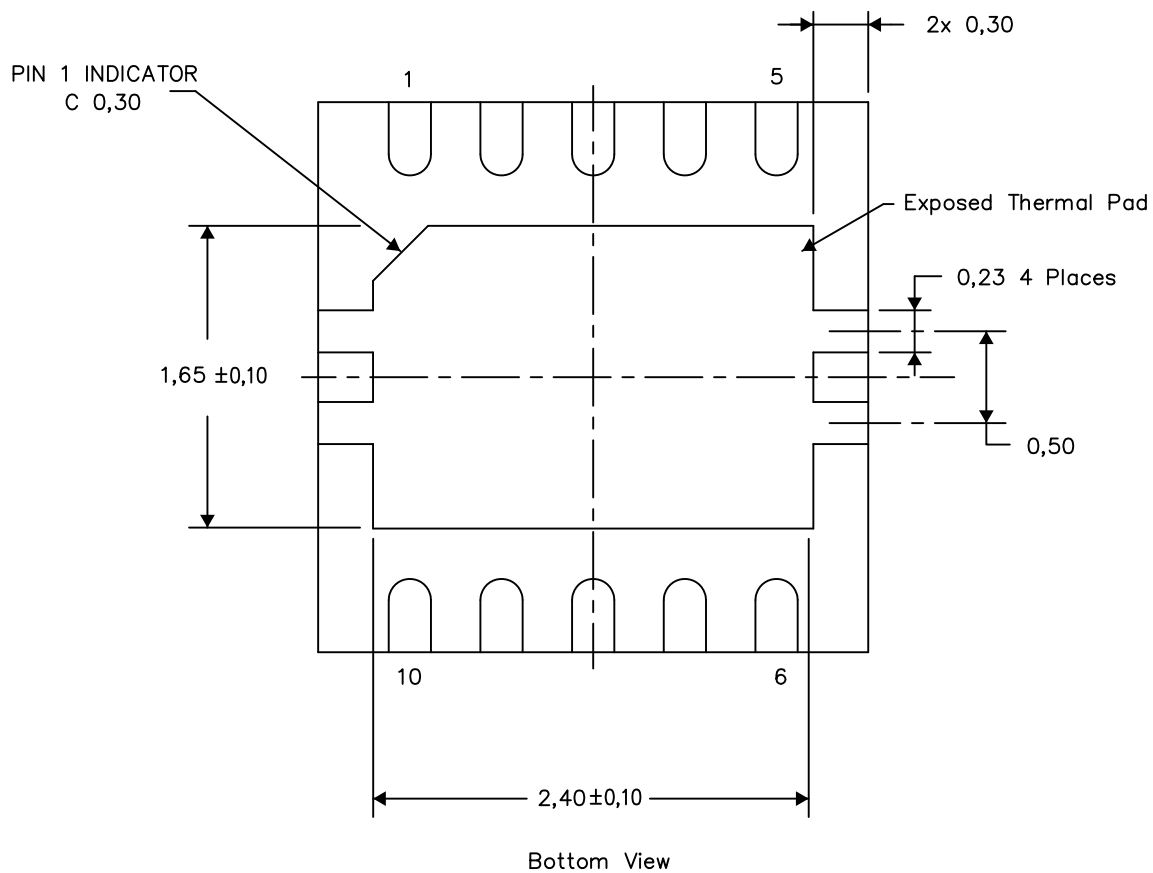
PLASTIC SMALL OUTLINE NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



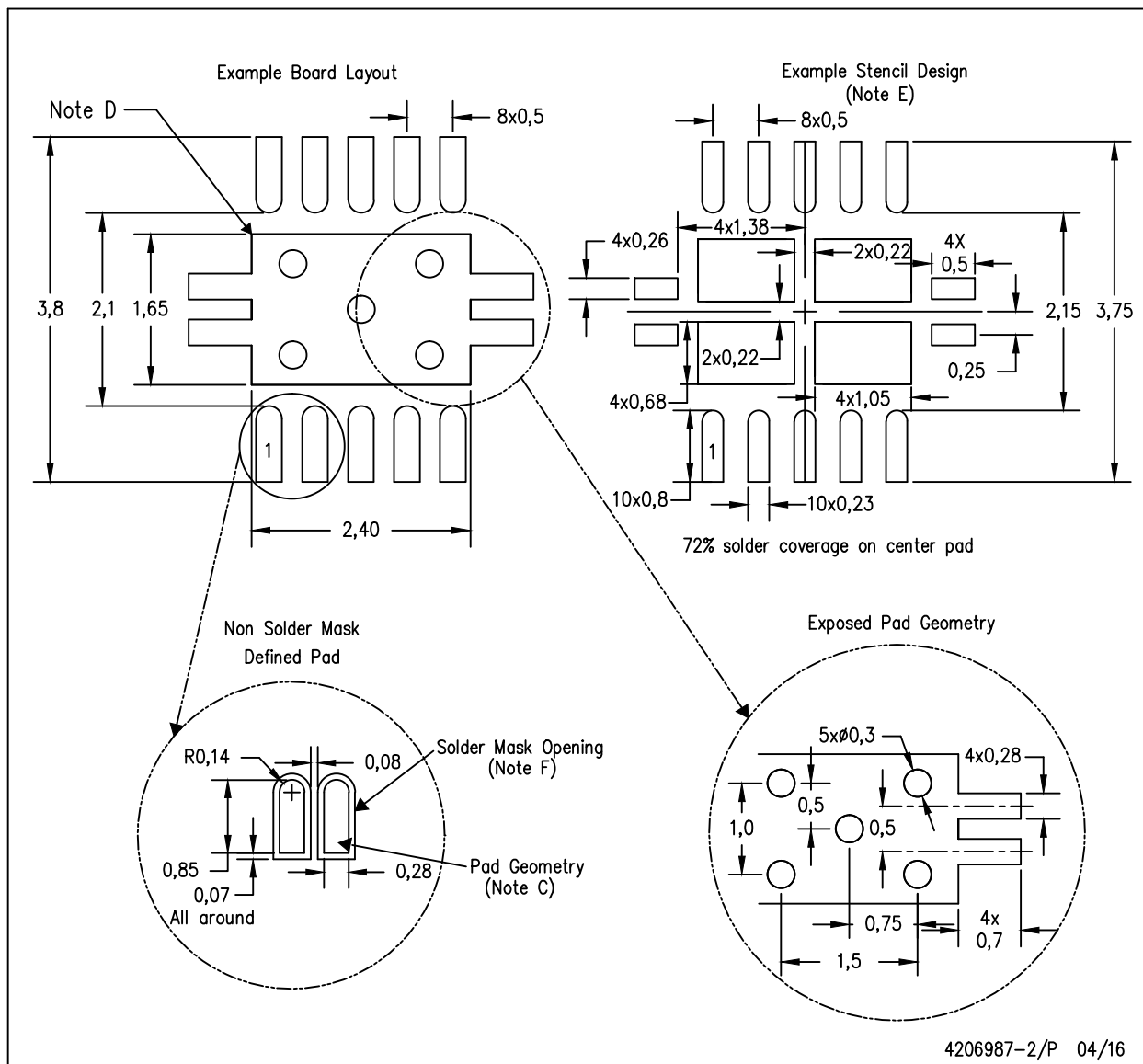
Exposed Thermal Pad Dimensions

4206565-3/Y 08/15

NOTE: A. All linear dimensions are in millimeters

DRC (S-PVSON-N10)

PLASTIC SMALL OUTLINE NO-LEAD



- NOTES:
- All linear dimensions are in millimeters.
 - This drawing is subject to change without notice.
 - Publication IPC-7351 is recommended for alternate designs.
 - This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <<http://www.ti.com>>.
 - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
 - Customers should contact their board fabrication site for minimum solder mask web tolerances between signal pads.

DRC (S-PVSON-N10)

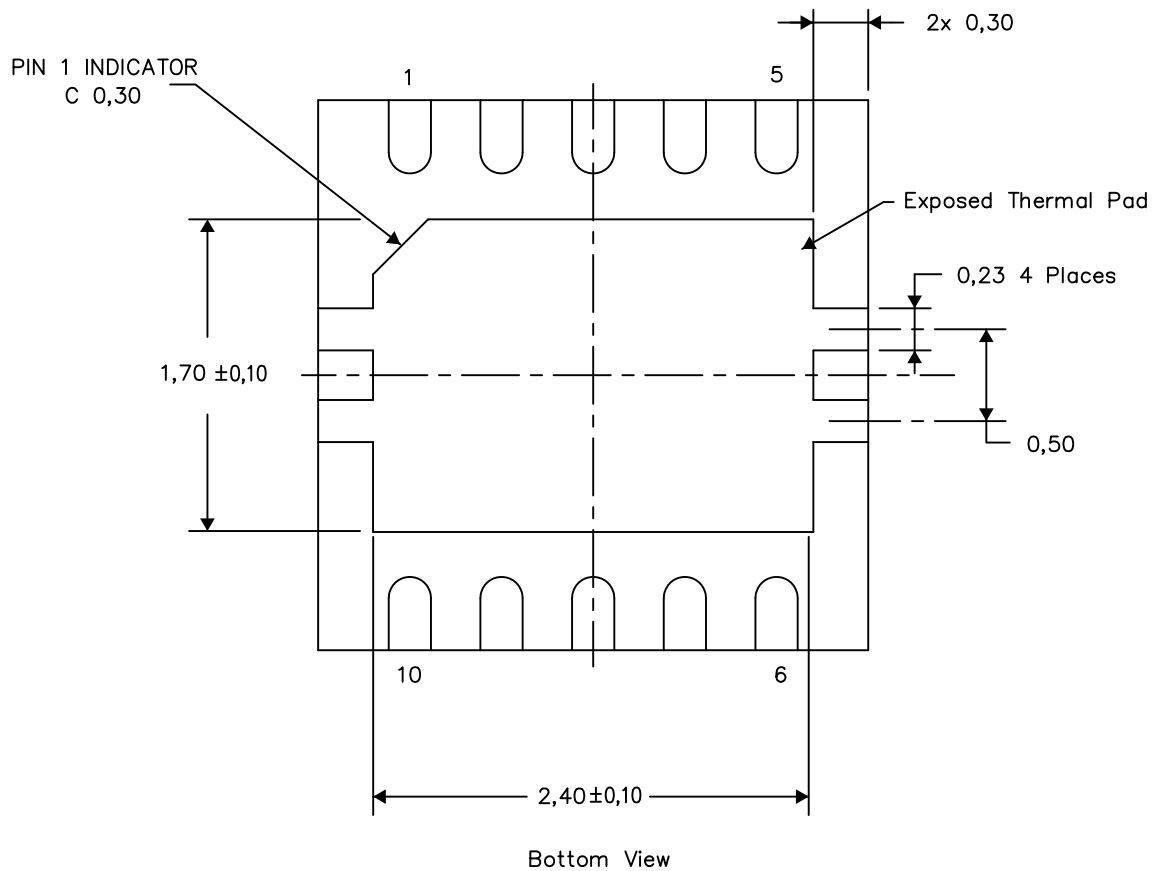
PLASTIC SMALL OUTLINE NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



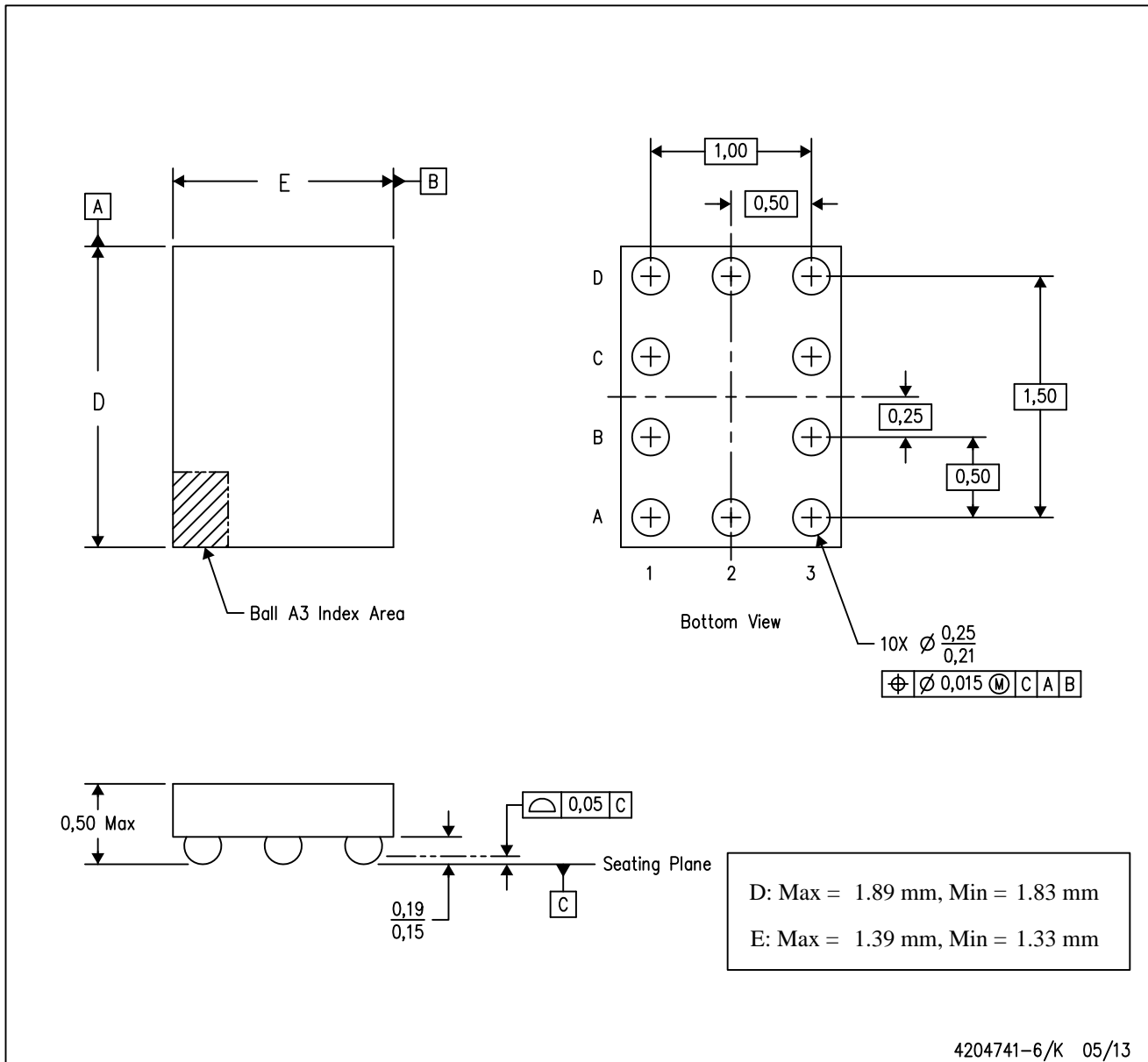
Exposed Thermal Pad Dimensions

4206565-8/Y 08/15

NOTE: A. All linear dimensions are in millimeters

YZP (R-XBGA-N10)

(CUSTOM) DIE-SIZE BALL GRID ARRAY



- NOTES:
- All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - This drawing is subject to change without notice.
 - NanoFree™ package configuration.

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Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have **not** been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

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